

Amendments to the Claims

This listing of claims replaces all prior versions and listings of claims in the application.

Listing of Claims

Claims 1-15 (canceled)

Claim 16 (currently amended) An active matrix circuit comprising:

a semiconductor layer;

a p-type impurity region provided in said semiconductor layer; **[[and]]**

[[an]] a first interlayer insulating film comprising silicon nitride provided over said semiconductor layer;

a conductive layer comprising titanium and aluminum over said first interlayer insulating film; and

a second interlayer insulating film provided over said conductive layer to provide a leveled upper surface over said semiconductor layer,

wherein said titanium and said aluminum are formed in a multi-layer film.

Claim 17 (previously presented): A circuit according to claim 16 wherein said active matrix circuit is incorporated into a liquid-crystal display.

Claim 18 (previously presented): A circuit according to claim 16 wherein said active matrix circuit is incorporated into an image sensor.

Claim 19 (previously presented): A circuit according to claim 16 wherein said active matrix circuit is incorporated into a liquid-crystal electro-optical device.

Claim 20 (previously presented): A circuit according to claim 16 wherein said semiconductor layer comprises a crystal silicon.

Claim 21 (currently amended): An active matrix circuit comprising:
a semiconductor layer;
a p-type impurity region provided in said semiconductor layer;
[[an]] a first interlayer insulating film comprising a silicon nitride layer and a silicon oxide layer, said first interlayer insulating film provided over said semiconductor layer;
a conductive layer comprising titanium and aluminum over said first interlayer insulating film; and
a second interlayer insulating film provided over said conductive layer to provide a leveled upper surface over said semiconductor layer.

Claim 22 (previously presented): A circuit according to claim 21 wherein said active matrix circuit is incorporated into a liquid-crystal display.

Claim 23 (previously presented): A circuit according to claim 21 wherein said active matrix circuit is incorporated into an image sensor.

Claim 24 (previously presented): A circuit according to claim 21 wherein said active matrix circuit is incorporated into a liquid-crystal electro-optical device

Claim 25 (previously presented): A circuit according to claim 21 wherein said semiconductor layer comprises a crystal silicon.

Claim 26 (currently amended): An active matrix circuit comprising:
a semiconductor layer;
a p-type impurity region provided in said semiconductor layer;

a first interlayer insulating film comprising silicon nitride provided over said semiconductor layer;

a conductive layer comprising titanium and aluminum over said first interlayer insulating film; and

a second interlayer insulating film provided over said conductive layer to provide a leveled upper surface over said semiconductor layer.

Claim 27 (previously presented): A circuit according to claim 26 wherein said conductive layer comprises an electrode.

Claim 28 (previously presented): A circuit according to claim 26 wherein said conductive layer comprises a wiring.

Claim 29 (previously presented): A circuit according to claim 26 wherein said active matrix circuit is incorporated into a liquid-crystal display.

Claim 30 (previously presented): A circuit according to claim 26 wherein said active matrix circuit is incorporated into an image sensor.

Claim 31 (previously presented): A circuit according to claim 26 wherein said active matrix circuit is incorporated into a liquid-crystal electro-optical device.

Claim 32 (previously presented): A circuit according to claim 26 wherein said semiconductor layer comprises a crystal silicon.

Claim 33 (cancelled).